EASY AXIS MAGNETIC AMPLIFIER

Abstract of the Disclosure

5

10

Techniques for improved semiconductor device performance are provided. In one aspect, a semiconductor device is provided. The device comprises at least one free magnetic layer, and a magnetic amplifier interacting with the free magnetic layer comprising two or more magnetic layers with at least one nonmagnetic layer therebetween. The nonmagnetic layer may be configured to provide parallel exchange coupling J of the magnetic layers in a range of $0 < J < \frac{4\pi \iota^2 M_3^2 n_y}{b}$, the magnetic layers having a long axis and a short axis, wherein t is a thickness of each magnetic layer, M_s is magnetization, n_y is a demagnetizing factor defined along the short axis of the magnetic layers and b is a diameter along a short axis of the magnetic layers. A method for switching a semiconductor device having at least one free magnetic layer is also provided.